



Super-resolution 3D tomography of vector near-fields in dielectric resonators

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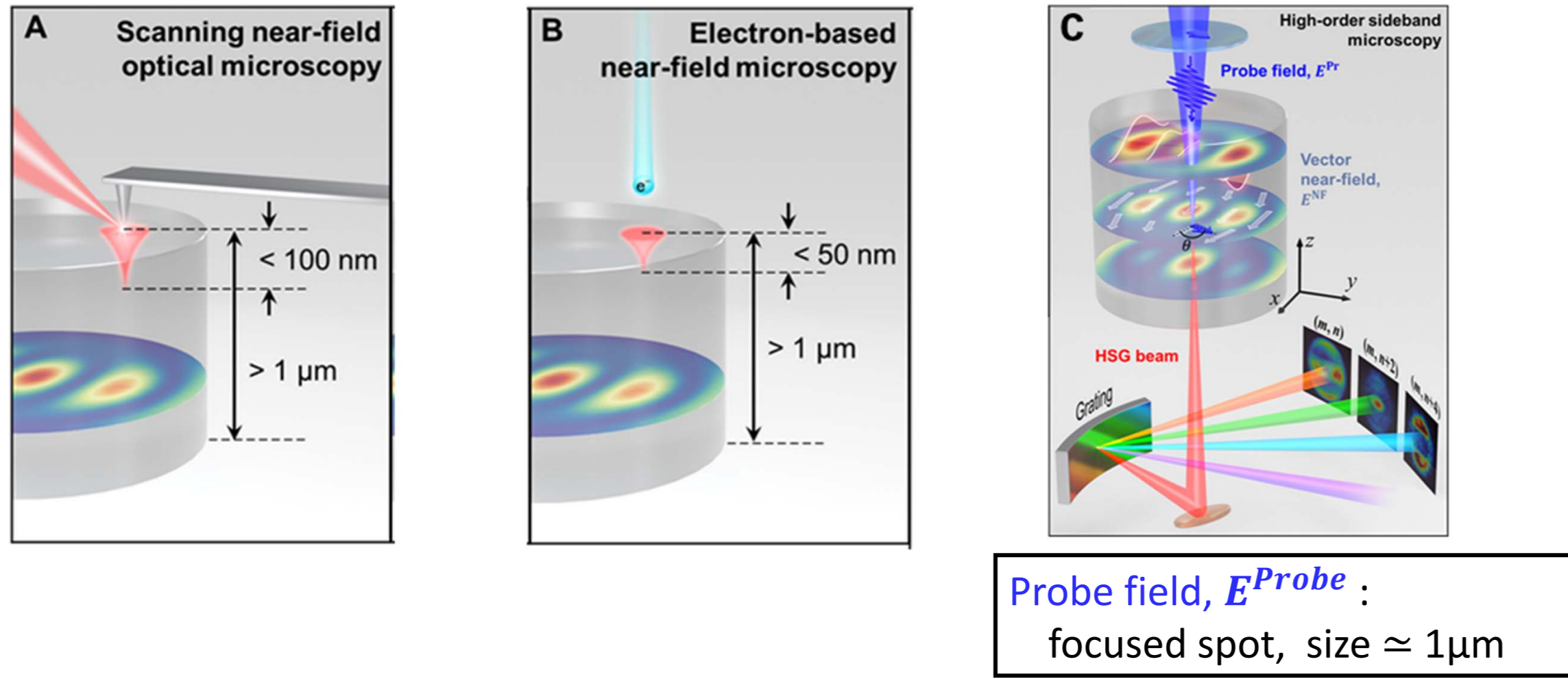
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I Introduction

How to image near-fields inside a dielectric resonator, E^{NF} ?

- tip-based (A) or electron-based (B): high resolution, but only surface sensitive
- Nonlinear optics: deep inside the dielectric!



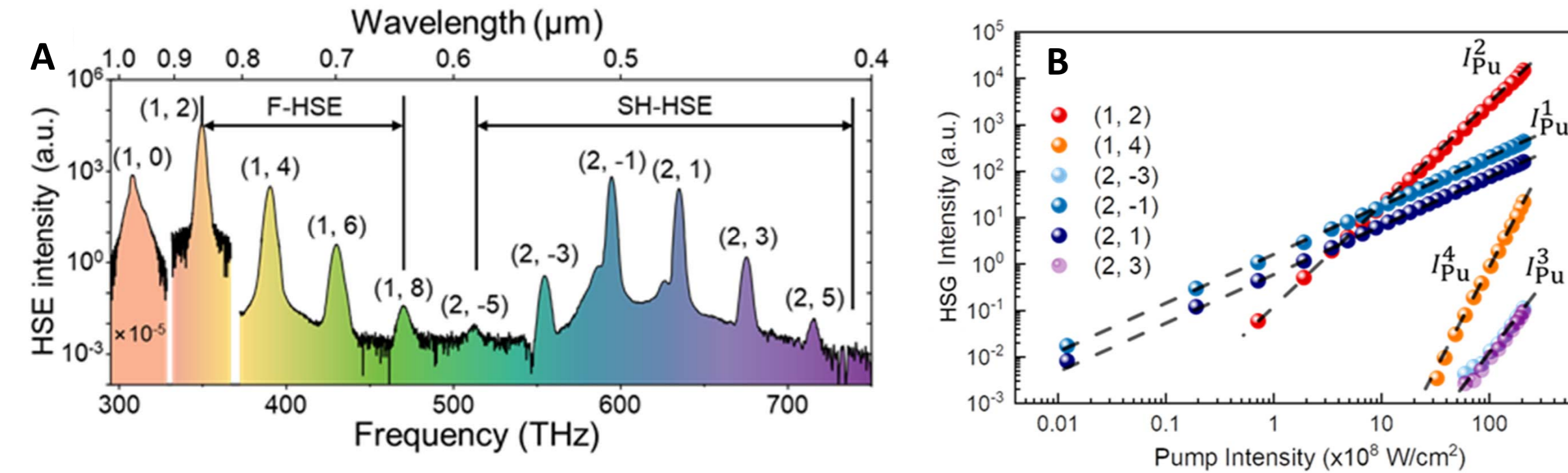
III Main Results

1. High-order sideband microscopy (HSM)

Nonlinear wave mixing: $P \propto \epsilon_0 \chi^{(m,n)} (E^{Probe})^m \cdot (E^{NF})^n$
 m-probe + n-near-field photons

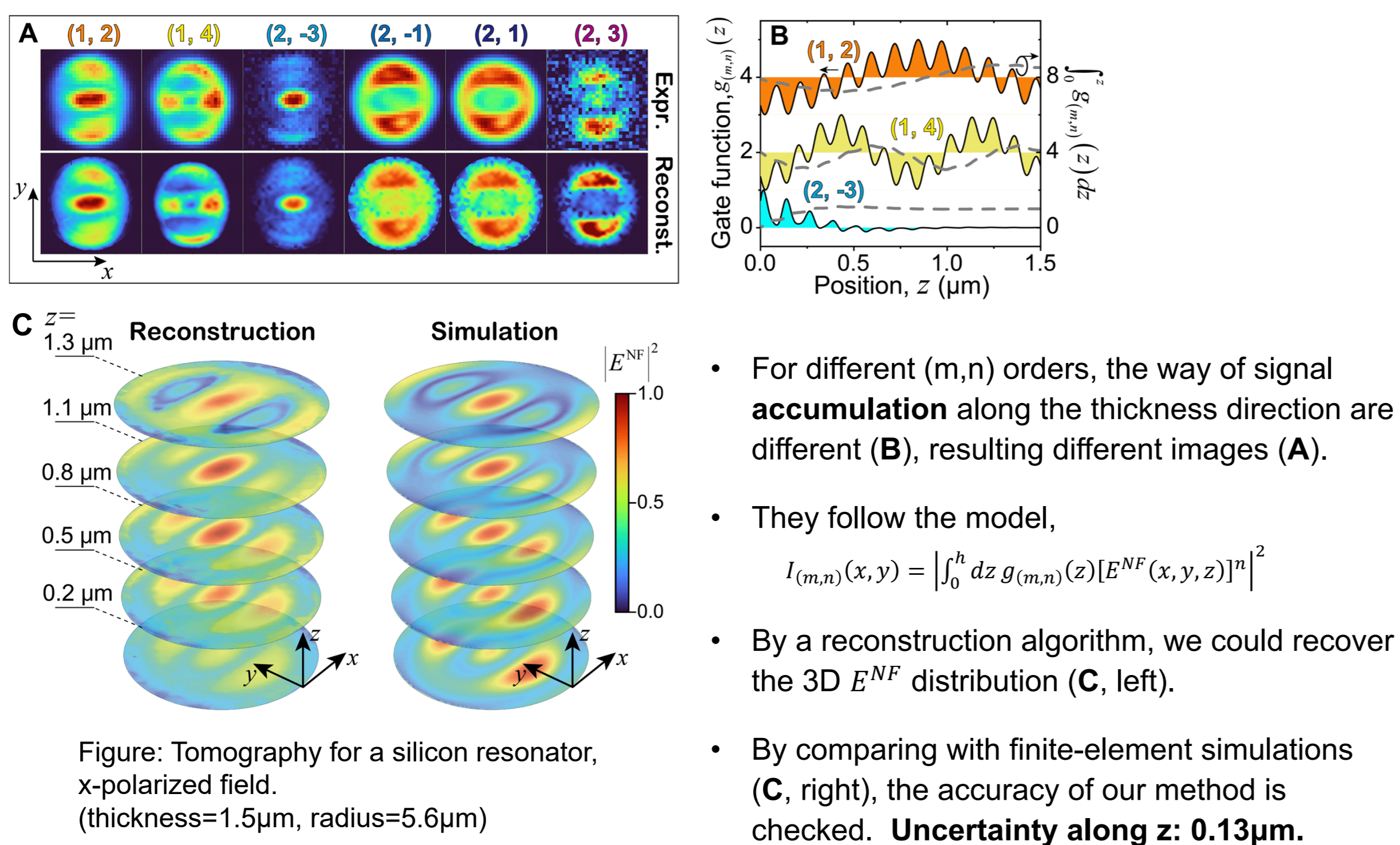
Radiated frequency: $f_{(m,n)} = mf_{Probe} + nf_{NF}$

Imaging " E^{NF} ": High-order sideband brings E^{NF} to the far field radiation!



A: typical sideband spectrum measured on 1.5μm-thick silicon film, probed at $\lambda_{Pu} = 0.97\mu\text{m}$, near-field excited at $\lambda_{NF} = 14\mu\text{m}$.
 B: energy-dependence of sidebands on the excitation (NF) intensity.

3. Tomography imaging

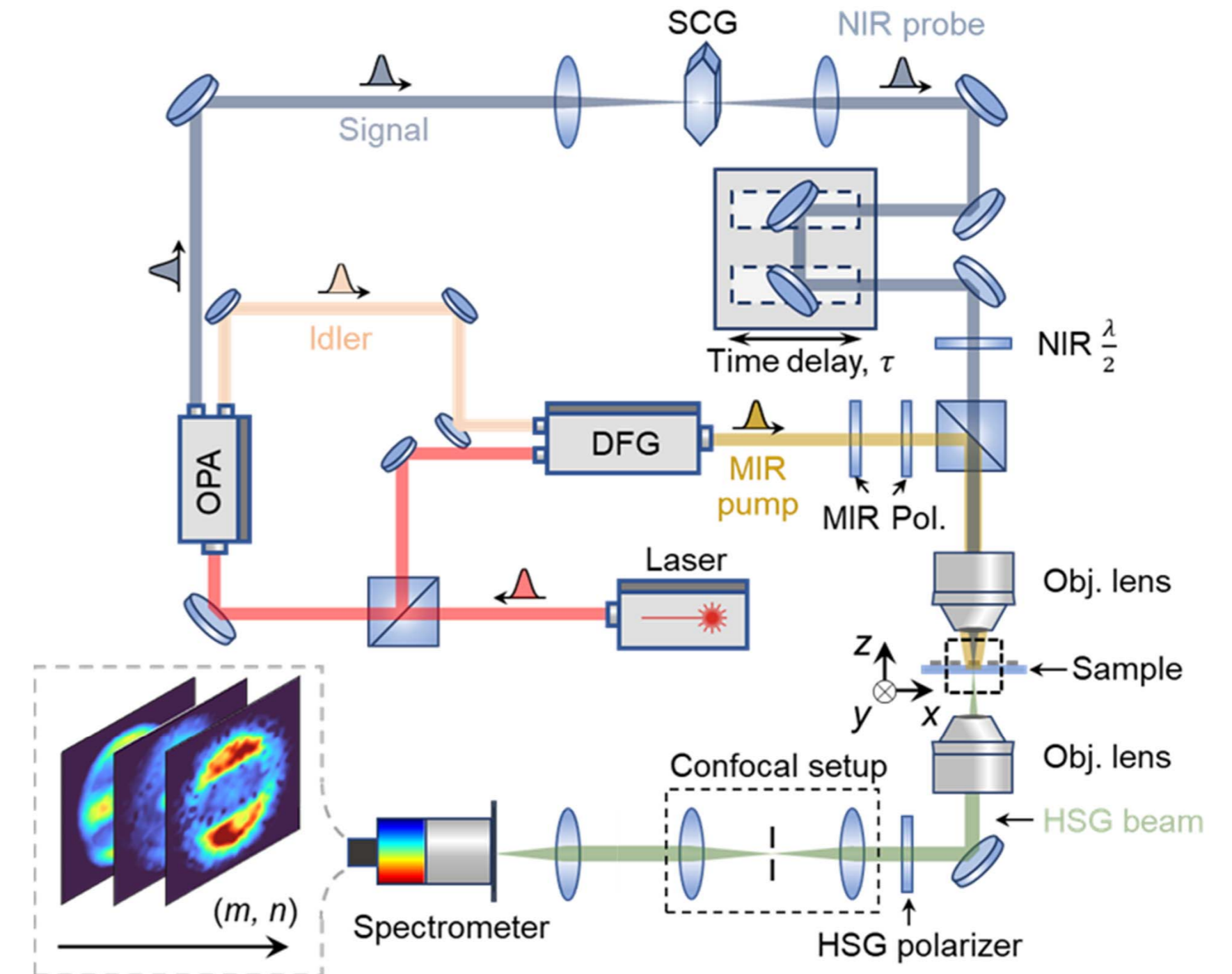


- For different (m,n) orders, the way of signal **accumulation** along the thickness direction are different (B), resulting different images (A).
- They follow the model,

$$I_{(m,n)}(x,y) = \left| \int_0^h dz g_{(m,n)}(z) [E^{NF}(x,y,z)]^m \right|^2$$
- By a reconstruction algorithm, we could recover the 3D E^{NF} distribution (C, left).
- By comparing with finite-element simulations (C, right), the accuracy of our method is checked. **Uncertainty along z: 0.13μm.**

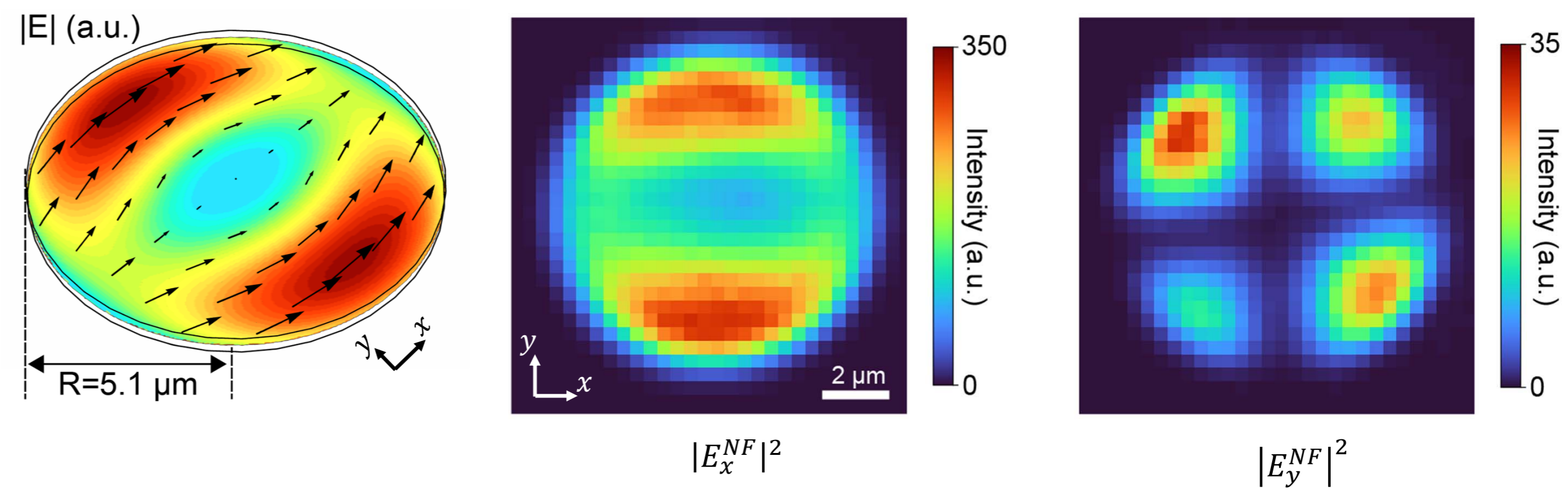
Figure: Tomography for a silicon resonator, x-polarized field, (thickness=1.5μm, radius=5.6μm)

II Experiment setup



- The near-field is excited by mid-infrared pulse (duration ~200 fs, $\lambda_{NF}=14\mu\text{m}$ and repetition rate 5 kHz), generated by the difference frequency process (DFG) in 500μm GaSe crystal.
- The probe pulse (~150fs, ~1μJ, $\lambda_{Pr}=0.97\mu\text{m}$) is generated from YAG supercontinuum, the **spectral range is tunable** by spectral bandpass filters.
- By focusing the pulses together on the sample, sideband harmonics are generated.
- Confocal geometry is applied, and **images are taken by scanning the sample transversely.**

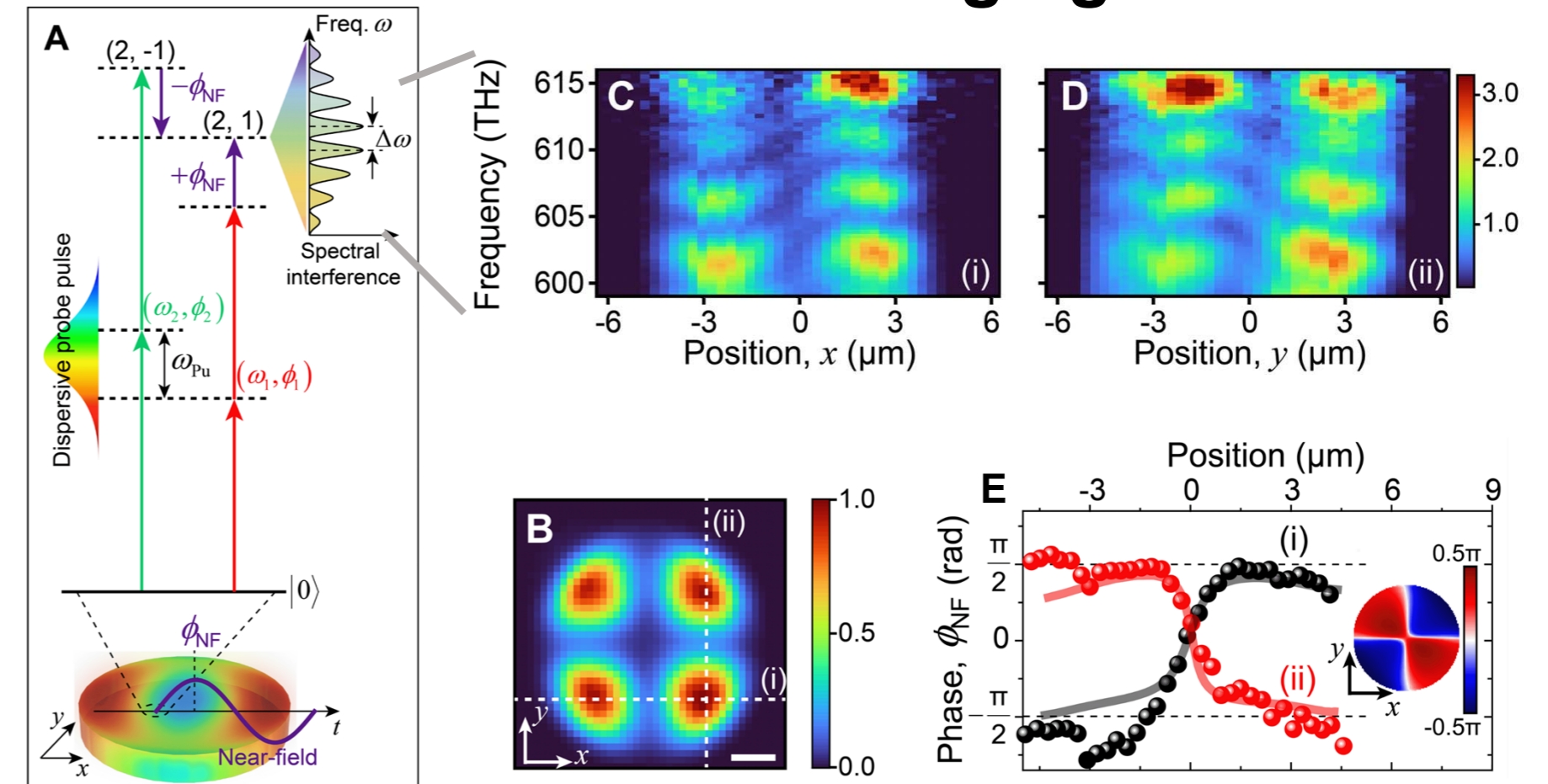
2. Polarization resolved near-field imaging



- **Left:** The near-field of a silicon resonator at $\lambda_{NF}=14\mu\text{m}$ excitation (radius=5.1μm, thickness=0.5μm)
- **Mid & right:** The x and y polarized components of near-field measured by HSM. **Resolution=0.9μm.**

How? Symmetry of tensor $\chi^{(m,n)}$ for order (m,n)=(2,1) → Sense different near-field polarizations by varying probe's polarization direction

4. Phase-resolved near-field imaging



- Resolving the near-field instantaneous phase by inter-sideband interference:**
- The probe pulse is broadband and dispersive, resulting spectral overlap between order (2, -1) and (2, 1). Spectral modulation patterns appear, which dependent on the near-field phase under detection.
 - We experimental scanned probe spot along trajectories (i) and (ii) for y-pol of near-field,
 - The spectral modulations for (i) and (ii) "shifted", which correspond to the variance of instantaneous near-field phase.
 - The measured instantaneous phases (dots) along (i) and (ii), compared with simulations (solid lines). Inset: simulated 2D phase distributions for the resonator.

VI Conclusion

- We demonstrate 3D tomographic, super-resolution and vector near-field imaging deep inside micrometer-thick dielectric optical resonators.
- The HSM technique demonstrated here could be applied to many other laser-induced wave phenomena beyond resonant near-fields. These include hyperbolic phonon-polaritons, topological photonic edge states, among others.